

ESD Protection Diode

Ultra-Low Capacitance Micro-Packaged Diodes for ESD Protection **ESD8472**

The ESD8472 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, high breakdown voltage, high linearity, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals.



• Industry Leading Capacitance Linearity Over Voltage

• Ultra-Low Capacitance: 0.2 pF • Insertion Loss: 0.030 dBm

• Small Footprint: 0.62 mm x 0.32 mm

• Stand-off Voltage: 5.3 V • Low Leakage: < 1 nA

• Low Dynamic Resistance: $< 1 \Omega$

• 1000 ESD IEC61000-4-2 Strikes ±8 kV Contact / Air Discharged

• SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable

• These Devices are Pb-Free, Halogen Free and are RoHS Compliant

Typical Applications

RF Signal ESD Protection

• RF Switching, PA, and Antenna ESD Protection

• Near Field Communications

• USB 2.0, USB 3.0

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
IEC 61000-4-2 Level 4 (Contact) (Note 1) IEC 61000-4-2 Level 4 (Air) (Note 1)	ESD	±20 ±20	kV
Maximum Peak Pulse Current IEC 61000-4-5 8/20 μs (Lightning) (Note 2)	I _{PP}	2.4	Α
Total Power Dissipation (Note 3) @ T _A = 25°C Thermal Resistance, Junction-to-Ambient	$P_{D} R_{ heta JA}$	300 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000-4-2 waveform.

2. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000-4-5 waveform.

3. Mounted with recommended minimum pad size, DC board FR-4





CASE 152AF

MARKING DIAGRAM

PIN 1 4M

4 = Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD8472MUT5G	X3DFN2 (Pb-Free)	10000 / Tape & Reel
SZESD8472MUT5G	X3DFN2 (Pb-Free)	10000 / Tape & Reel

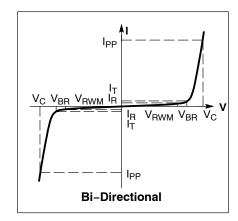
[†]For information on tape and reel specifications. including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
I _T	Test Current

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}				5.3	V
Breakdown Voltage	V_{BR}	I _T = 1 mA (Note 4)	7.0		12	V
Reverse Leakage Current	I _R	V _{RWM} = 5.3 V		< 1	50	nA
Clamping Voltage	V _C	I _{PP} = 1 A (Note 5)		11	15	V
Clamping Voltage	V _C	I _{PP} = 2.4 A (Note 5)		15	17.8	V
ESD Clamping Voltage	V _C	Per IEC61000-4-2	See Figures 1 and 2			
Junction Capacitance	CJ	$V_R = 0 \text{ V, } f = 1 \text{ MHz}$ $V_R = 0 \text{ V, } f = 1 \text{ GHz}$		0.20 0.15	0.30 0.30	pF
Dynamic Resistance	R _{DYN}	TLP Pulse		0.75		Ω
Insertion Loss		f = 1 MHz f = 8.5 GHz		0.050 0.250		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
- 5. Non-repetitive current pulse at 25°C, per IEC61000-4-5 waveform (Figure 9).

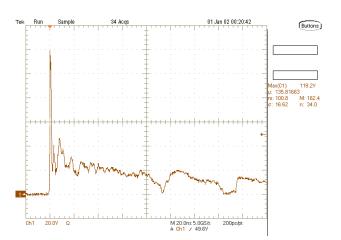


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

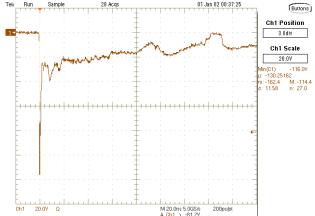


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

ESD8472

TYPICAL CHARACTERISTICS

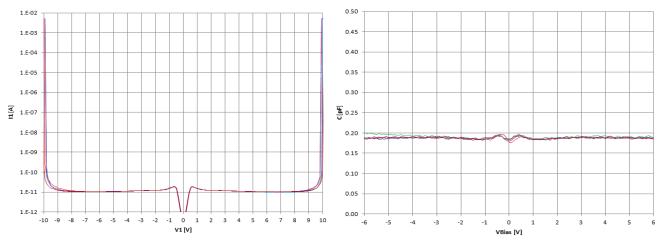


Figure 3. IV Characteristics

Figure 4. CV Characteristics

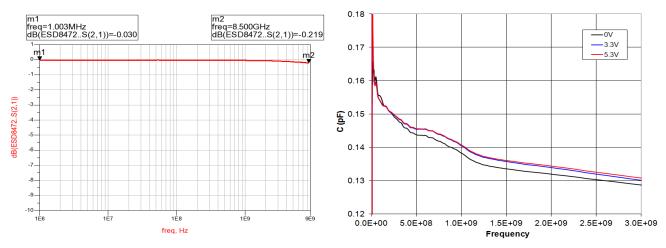


Figure 5. RF Insertion Loss

Figure 6. Capacitance over Frequency

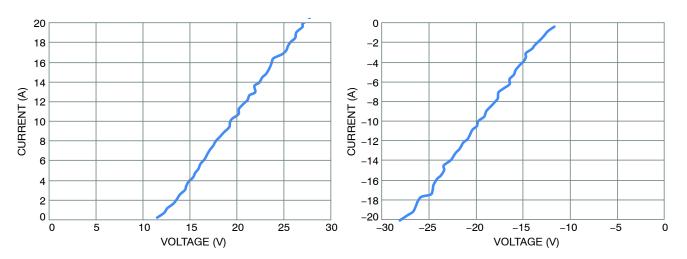


Figure 7. Positive TLP I-V Curve

Figure 8. Negative TLP I-V Curve

ESD8472

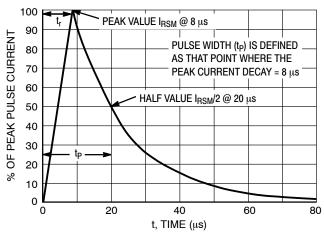


Figure 9. IEC 61000-4-5 8/20 μs Pulse Waveform

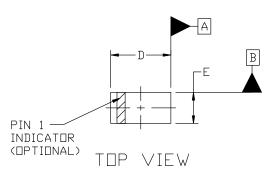


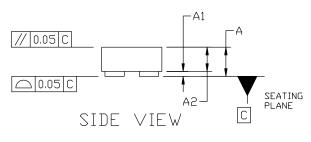


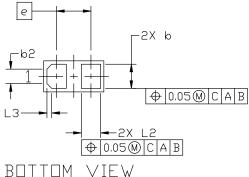
X3DFN2 0.62x0.32x0.24, 0.35P

CASE 152AF ISSUE C

DATE 08 AUG 2023







GENERIC MARKING DIAGRAM*



X = Specific Device Code

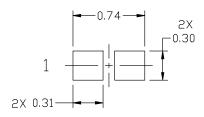
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 0201

	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	0.25	0.29	0.33
A1	0.00		0.05
A2	0.14	0.24	0.34
b	0.22	0.25	0.28
b2	0.150 REF		
D	0.58	0.62	0.66
E	0.28	0.32	0.36
е	0.355 BSC		
L2	0.17	0.20	0.23
L3	0.050 REF		



RECOMMENDED MOUNTING FOOTPRINT*

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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DESCRIPTION:	X3DFN2 0.62x0.32x0.24, 0.35P		PAGE 1 OF 1	

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